

Amendments to Specification

At page 1 in the specification as originally filed, after the Title of the Invention, please insert the following new paragraph:

-- RELATED APPLICATIONS

This application is a § 371 National Phase Application of PCT/CH2005/000184, filed on March 31, 2005, and claims priority to European Application No. EP 04007760.4, filed on March 31, 2004, both of which are incorporated herein by reference in their entirety.--

Replace the paragraph beginning at page 2, line 17, in the specification as originally filed, with the following rewritten paragraph:

--The image-sensor pixels known from literature are either of the photodiode or the metal-oxide-semiconductor (MOS) device type, as described for example in P. Scitz, "Solid-State Image Sensing", in Computer Vision and Applications--A Guide for Students and Practitioners (B. Jahne and H. Haussecker, Eds.), pp. 111-[[152]] 151, Academic Press, San Diego, 2000. In such photosensors, the photocharge-detection sensitivity varies with the inverse of the pixel's capacitance. This capacitance, on the other hand, increases in direct proportion with the pixel area. For this reason, it is not possible to realize such conventional photosensors that are at the same time very large, highly sensitive and fast.--